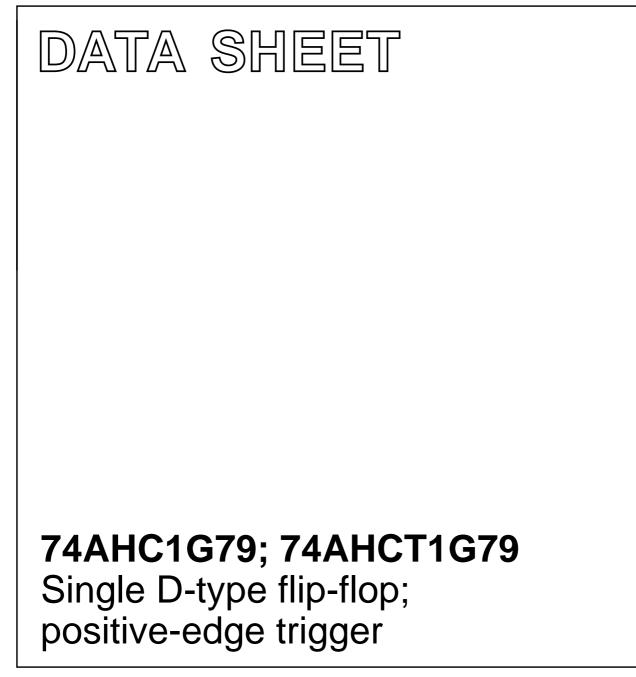
INTEGRATED CIRCUITS



Product specification Supersedes data of 2002 Feb 18 2002 Jun 06







FEATURES

- Symmetrical output impedance
- High noise immunity
- ESD protection:
 - HBM EIA/JESD22-A114-A exceeds 2000 V
 - MM EIA/JESD22-A115-A exceeds 200 V
 - CDM EIA/JESD22-C101 exceeds 1000 V.
- Low power dissipation
- Balanced propagation delays
- Multiple very small 5 pin packages
- Output capability: standard
- Specified from -40 to +125 °C.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25 \text{ °C}$; $t_r = t_f \le 3.0 \text{ ns.}$

74AHC1G79; 74AHCT1G79

DESCRIPTION

The 74AHC1G/AHCT1G79 is a high-speed Si-gate CMOS device.

The 74AHC1G/AHCT1G79 provides a single positive-edge triggered D-type flip-flop.

Information on the data input is transferred to the Q output on the LOW-to-HIGH transition of the clock pulse. The D input must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

SYMBOL	PARAMETER	CONDITIONS	ТҮР	UNIT	
		CONDITIONS	AHC1G	AHCT1G	
t _{PHL} /t _{PLH}	propagation delay CP to Q	$C_{L} = 15 \text{ pF}; V_{CC} = 5 \text{ V}$	3.5	3.5	ns
CI	input capacitance		1.5	1.5	pF
C _{PD}	power dissipation capacitance	$C_L = 50 \text{ pF}; f = 1 \text{ MHz};$ notes 1 and 2	15	16	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

2. The condition is $V_I = GND$ to V_{CC} .

74AHC1G79; 74AHCT1G79

FUNCTION TABLE

See note 1.

INP	INPUTS					
СР	D	Q + 1				
<u>↑</u>	L	L				
<u>↑</u>	Н	Н				
L	Х	Q				

Note

1. H = HIGH voltage level;

L = LOW voltage level;

 \uparrow = LOW-to-HIGH CP transition;

X = don't care;

Q + 1 = state after the next LOW-to-HIGH CP transition.

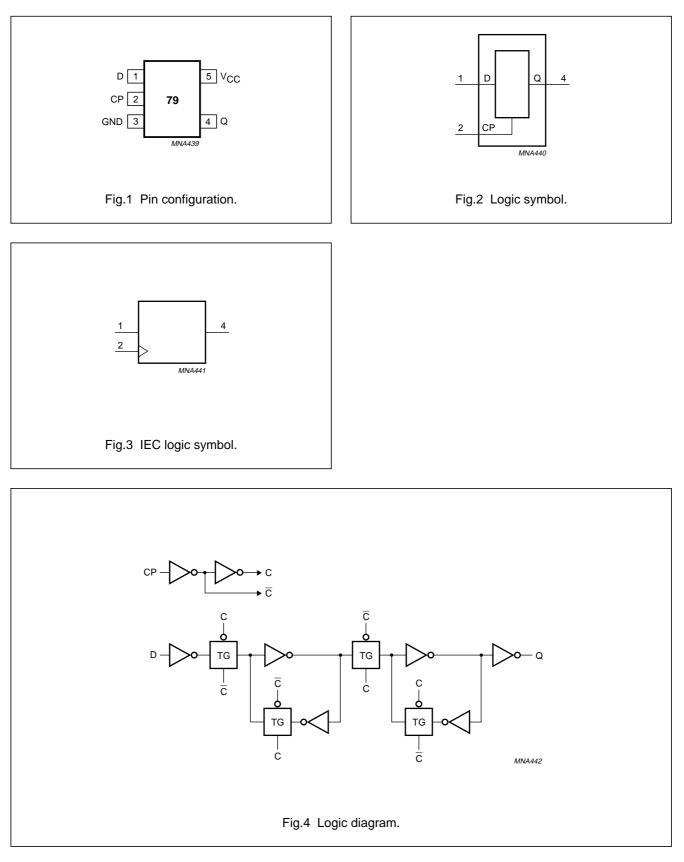
ORDERING INFORMATION

	PACKAGE									
TYPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING				
74AHC1G79GW	–40 to +125 °C	5	SC-88A	plastic	SOT353	AP				
74AHCT1G79GW	–40 to +125 °C	5	SC-88A	plastic	SOT353	СР				
74AHC1G79GV	–40 to +125 °C	5	SC-74A	plastic	SOT753	A79				
74AHCT1G79GV	–40 to +125 °C	5	SC-74A	plastic	SOT753	C79				

PINNING

PIN	SYMBOL	DESCRIPTION					
1	D	data input D					
2	СР	clock pulse input CP					
3	GND	ground (0 V)					
4	Q	data output Q					
5	V _{CC}	supply voltage					

74AHC1G79; 74AHCT1G79



74AHC1G79; 74AHCT1G79

RECOMMENDED OPERATING CONDITIONS

SYMBOL PARAMET			74AHC1G			7			
	PARAMETER	ER CONDITIONS		TYP.	MAX.	MIN.	TYP.	MAX.	UNIT
V _{CC}	supply voltage		2.0	5.0	5.5	4.5	5.0	5.5	V
VI	input voltage		0	_	5.5	0	-	5.5	V
Vo	output voltage		0	_	V _{CC}	0	-	V _{CC}	V
T _{amb}	operating ambient temperature	see DC and AC characteristics per device	-40	+25	+125	-40	+25	+125	°C
t _r , t _f	input rise and fall	V _{CC} = 3.3 ±0.3 V	-	-	100	-	-	_	ns/V
$(\Delta t/\Delta f)$	times	V _{CC} = 5 ±0.5 V	-	-	20	-	-	20	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	PARAMETER CONDITIONS		MAX.	UNIT
V _{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input diode current	$V_{1} < -0.5 V$	-	-20	mA
I _{ОК}	output diode current	V_{O} < -0.5 or V_{O} > V_{CC} + 0.5 V; note 1	-	±20	mA
I _O	output source or sink current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	V _{CC} or GND current		-	±75	mA
T _{stg}	storage temperature		-65	+150	°C
PD	power dissipation per package	for temperature range from -40 to $+125 \ ^\circ C$	-	250	mW

Note

1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

74AHC1G79; 74AHCT1G79

DC CHARACTERISTICS

Family 74AHC1G

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDITI	ONS			٦	Г _{ать} (°С	;)			
SYMBOL	PARAMETER	071155	V _{cc}		25		-40 t	o +85	-40 to	o +125	UNIT
		OTHER	(V)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input		2.0	1.5	-	-	1.5	-	1.5	-	V
	voltage		3.0	2.1	-	_	2.1	-	2.1	-	V
			5.5	3.85	-	-	3.85	-	3.85	-	V
V _{IL}	LOW-level input		2.0	-	-	0.5	-	0.5	-	0.5	V
	voltage		3.0	-	-	0.9	-	0.9	-	0.9	V
			5.5	-	-	1.65	-	1.65	-	1.65	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -50 \ \mu\text{A}$	2.0	1.9	2.0	-	1.9	-	1.9	-	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -50 \ \mu\text{A}$	3.0	2.9	3.0	-	2.9	-	2.9	-	V
	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -50 \ \mu\text{A}$	4.5	4.4	4.5	-	4.4	-	4.4	-	V	
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -4.0 \text{ mA}$	3.0	2.58	-	-	2.48	-	2.40	-	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -8.0 \text{ mA}$	4.5	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 50 \ \mu\text{A}$	2.0	-	0	0.1	-	0.1	-	0.1	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 50 \ \mu\text{A}$	3.0	-	0	0.1	-	0.1	-	0.1	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 50 \ \mu\text{A}$	4.5	-	0	0.1	-	0.1	-	0.1	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 4.0 \text{ mA}$	3.0	-	-	0.36	-	0.44	-	0.55	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 8.0 \text{ mA}$	4.5	-	-	0.36	-	0.44	-	0.55	V
I _{LI}	input leakage current	$V_{I} = V_{CC}$ or GND	5.5	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	quiescent supply current	$V_{I} = V_{CC} \text{ or } GND;$ $I_{O} = 0$	5.5	-	-	1.0	-	10	-	40	μA
CI	input capacitance			-	1.5	10	-	10	-	10	pF

74AHC1G79; 74AHCT1G79

Family 74AHCT1G

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDI	TIONS			٦	Г _{ать} (°С	C)			
SYMBOL	PARAMETER	OTUED	V 00		25		-40 t	o +85	-40 te	o +125	
		OTHER	V _{CC} (V)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
V _{IH}	HIGH-level input voltage		4.5 to 5.5	2.0	-	-	2.0	_	2.0	-	V
V _{IL}	LOW-level input voltage		4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -50 \ \mu\text{A}$	4.5	4.4	4.5	-	4.4	-	4.4	-	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = -8.0 \text{ mA}$	4.5	3.94	-	-	3.8	-	3.70	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 50 \ \mu\text{A}$	4.5	-	0	0.1	-	0.1	-	0.1	V
		$V_{I} = V_{IH} \text{ or } V_{IL};$ $I_{O} = 8.0 \text{ mA}$	4.5	-	-	0.36	-	0.44	-	0.55	V
ILI	input leakage current	$V_{I} = V_{IH} \text{ or } V_{IL}$	5.5	-	-	0.1	-	1.0	-	2.0	μA
I _{CC}	quiescent supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$	5.5	-	-	1.0	-	10	-	40	μA
ΔI _{CC}	additional quiescent supply current per input pin	$V_{I} = 3.4 \text{ V};$ other inputs at $V_{CC} \text{ or GND};$ $I_{O} = 0$	5.5	-	-	1.35	-	1.5	-	1.5	mA
CI	input capacitance			-	1.5	10	-	10	_	10	pF

74AHC1G79; 74AHCT1G79

AC CHARACTERISTICS

Type 74AHC1G79

GND = 0 V; $t_r = t_f \le 3.0$ ns.

		TEST CONDITI	ONS	T _{amb} (°C)							
SYMBOL PARA	PARAMETER	WAVEFORMS	CL	25			-40 to +85		-40 to +125		UNIT
		WAVEFORMS	(pF)	MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
V _{CC} = 3.0 t	t o 3.6 V; note 1		•				•				
t _{PHL} /t _{PLH}		see Figs 5 and 6	15	_	4.9	8.4	1.0	9.8	1.0	11.5	ns
	CP to Q		50	_	6.9	12.0	1.0	14.0	1.0	15.5	ns
V _{CC} = 4.5 t	to 5.5 V; note 2	·		-							
t _{PHL} /t _{PLH}	propagation delay	see Figs 5 and 6	15	_	3.5	5.6	1.0	7.0	1.0	8.0	ns
	CP to Q		50	_	5.1	8.0	1.0	10.0	1.0	11.0	ns
t _{su}	set-up time D to CP			3.0	1.0	-	3.0	-	4.0	-	ns
t _h	hold time D to CP			+2.0	-1.0	-	2.0	-	3.0	-	ns
t _W	clock pulse width HIGH or LOW			3.0	-	-	3.0	-	4.0	-	ns
f _{max}	maximum clock pulse frequency			90	_	-	90	-	70	-	MHz

Notes

1. Typical values are measured at V_{CC} = 3.3 V.

2. Typical values are measured at V_{CC} = 5.0 V.

Type 74AHCT1G79

 $GND = 0 \text{ V}; \ t_r = t_f \leq 3.0 \text{ ns}.$

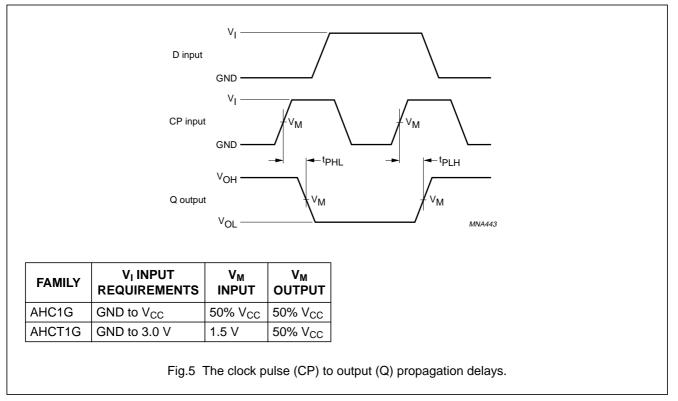
		TEST CONDITI	TEST CONDITIONS		T _{amb} (°C)						
SYMBOL	PARAMETER		C _L (pF)	25			-40 to +85		-40 to +125		
		WAVEFORMS		MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	1
V _{CC} = 4.5 t	to 5.5 V; note 1	•			•						
t _{PHL} /t _{PLH}	PLH propagation delay	see Figs 5 and 6	15	-	3.5	5.0	1.0	6.0	1.0	8.0	ns
	CP to Q		50	-	5.0	8.0	1.0	10.0	1.0	11.0	ns
t _{su}	set-up time D to CP			3.0	1.0	-	3.0	-	4.0	-	ns
t _h	hold time D to CP			+2.0	-1.0	-	0	-	3.0	-	ns
t _W	clock pulse width HIGH or LOW			3.0	-	-	3.0	-	4.0	-	ns
f _{max}	maximum clock pulse frequency			90	-	-	90	-	70	-	MHz

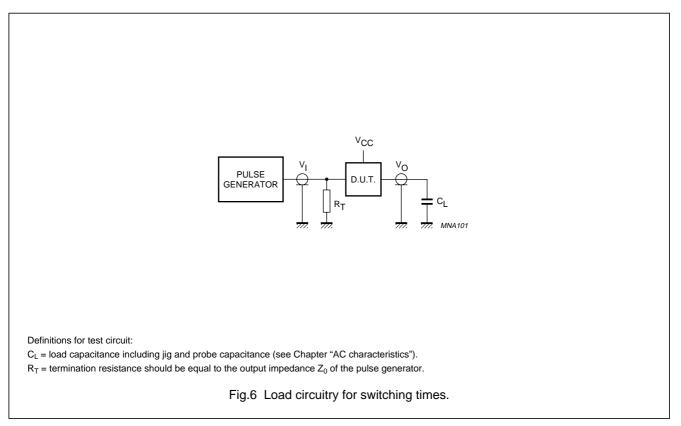
Note

1. Typical values are measured at $V_{CC} = 5 V$.

74AHC1G79; 74AHCT1G79

AC WAVEFORMS

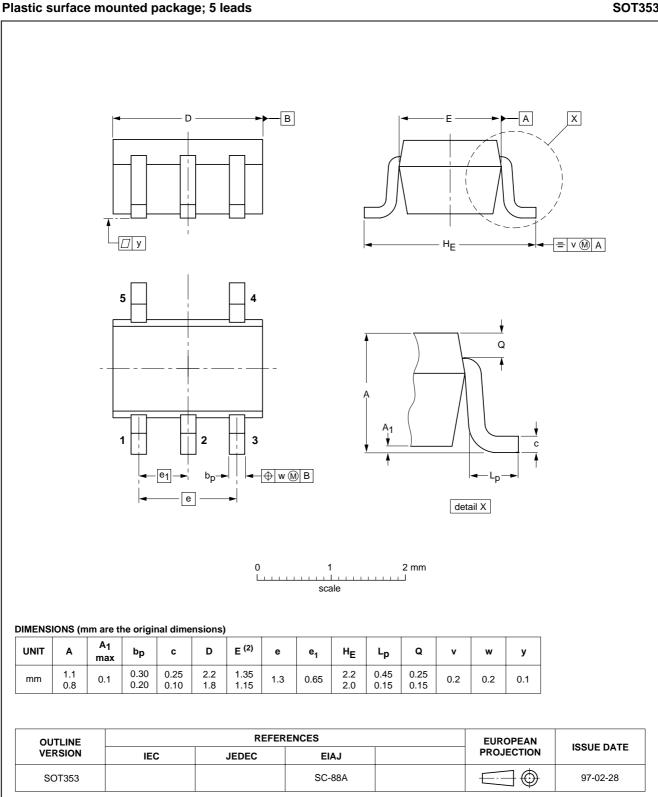




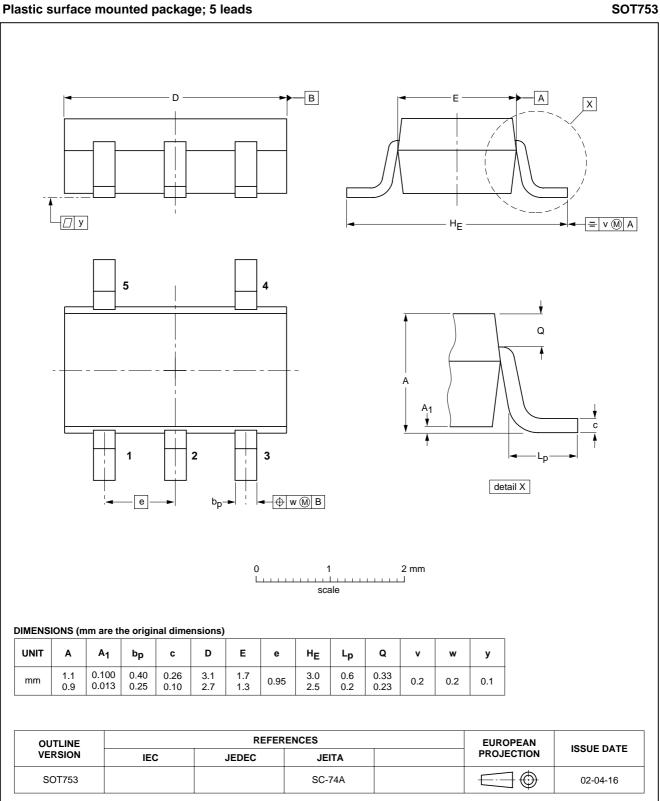
74AHC1G79; 74AHCT1G79

Single D-type flip-flop; positive-edge trigger

PACKAGE OUTLINES



74AHC1G79; 74AHCT1G79



Plastic surface mounted package; 5 leads

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

74AHC1G79; 74AHCT1G79

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^\circ\text{C}.$

74AHC1G79; 74AHCT1G79

Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE ⁽¹⁾	SOLDERING METHOD				
FACKAGE	WAVE	REFLOW ⁽²⁾			
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable			
HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽³⁾	suitable			
PLCC ⁽⁴⁾ , SO, SOJ	suitable	suitable			
LQFP, QFP, TQFP	not recommended ⁽⁴⁾⁽⁵⁾	suitable			
SSOP, TSSOP, VSO	not recommended ⁽⁶⁾	suitable			

Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 6. Wave soldering is suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

74AHC1G79; 74AHCT1G79

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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